

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional Patent Application of)
Hongyong ZHANG et al.)
Application No. 08/611,571) Art Unit: 2829
Filed: March 6, 1996) Examiner: E. Pert
For: THIN-FILM TRANSISTOR) Date: August 18, 2003

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Please preliminarily amend the subject application as follows:

IN THE SPECIFICATION:

Page 31, replace the first full paragraph with the follow:

--Next on the semiconductor layer 14, an aluminum layer, as source and drain electrodes, is formed, patterning is performed, and the source and drain impurity regions 14 and 14', as well as the source and drain electrodes 16 and 16', are formed, wherein the semiconductor device is completed after the formation of insulating portion 40.--.

Page 32, replace the third full paragraph with the following:

-- Furthermore, FET is mentioned here but this invention is not limited to FET but can also be used in the insulated film of other semiconductor devices such as DRAM. Also in the above embodiments the insulation film used is SiO₂, however, according to specific needs, alumina, tantalum oxide, barium titanate, or silicon nitride can be used in the same way.--